NTNUS3171PZ

[MOSFET](#) – Single P-Channel, Small Signal, SOT-1123, 1.0 x 0.6 mm

-20 V, -200 mA

ON Semiconductor®

http://onsemi.com

Features

- Single P−Channel MOSFET
- Offers a Low $R_{DS(on)}$ Solution in the Ultra Small 1.0 x 0.6 mm Package
- 1.5 V Gate Voltage Rating
- Ultra Thin Profile (< 0.5 mm) Allows It to Fit Easily into Extremely Thin Environments such as Portable Electronics.
- This is a Pb−Free Device

Applications

- High Side Switch
- High Speed Interfacing
- Optimized for Power Management in Ultra Portable Equipment

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX	I_D Max
−20 V	3.5 Ω @ −4.5 V	−0.20 A
	4.0 Ω @ −2.5 V	
	5.5 Ω @ −1.8 V	
	7.0 Ω @ −1.5 V	
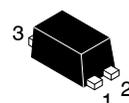
SOT−1123
CASE 524AA

MARKING DIAGRAM

5 M
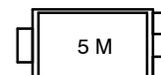
5 = Specific Device Code
(Rotated 90° Clockwise)
M = Date Code

P−Channel MOSFET

MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

Parameter			Symbol	Value	Unit
Drain−to−Source Voltage			V_{DSS}	−20	V
Gate−to−Source Voltage			V_{GS}	±8	V
Continuous Drain Current (Note 1)	Steady State	T_A = 25°C	I_D	−150	mA
		T_A = 85°C		−110	
	t ≤ 5 s	T_A = 25°C		−200	
Power Dissipation (Note 1)	Steady State	T_A = 25°C	P_D	−125	mW
	t ≤ 5 s			−200	
Pulsed Drain Current	t_p = 10 μs		I_{DM}	−600	mA
Operating Junction and Storage Temperature			T_J, T_{STG}	−55 to 150	°C
Source Current (Body Diode) (Note 2)			I_S	−200	mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface−mounted on FR4 board using the minimum recommended pad size, or 2 mm^2, 1 oz Cu.
2. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%

ORDERING INFORMATION

Device	Package	Shipping†
NTNUS3171PZT5G	SOT−1123 (Pb−Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

THERMAL RESISTANCE RATINGS

| Parameter	Symbol	Max	Unit
Junction−to−Ambient − Steady State (Note 3)	$R_{\theta JA}$	1000	°C/W
Junction−to−Ambient − t = 5 s (Note 3)	$R_{\theta JA}$	600	

3. Surface−mounted on FR4 board using the minimum recommended pad size, or 2 mm², 1 oz Cu.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = −250 μA		−20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{GS} = 0 V, V_{DS} = −5.0 V	T_J = 25°C			−50	nA
		V_{GS} = 0 V, V_{DS} = −5.0 V	T_J = 85°C			−100	
		V_{GS} = 0 V, V_{DS} = −16 V	T_J = 25°C			−200	
Gate−to−Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±5.0 V				±100	nA
ON CHARACTERISTICS (Note 4)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = −250 μA		−0.4	−0.7	−1.0	V
Drain−to−Source On Resistance	$R_{DS(ON)}$	V_{GS} = −4.5 V, I_D = −100 mA			2.0	3.5	Ω
		V_{GS} = −2.5 V, I_D = −50 mA			2.6	4.0	
		V_{GS} = −1.8 V, I_D = −20 mA			3.4	5.5	
		V_{GS} = −1.5 V, I_D = −10 mA			4.0	7.0	
		V_{GS} = −1.2 V, I_D = −1.0 mA			6.0		
Forward Transconductance	g_{FS}	V_{DS} = −5.0 V, I_D = −125 mA			0.26		S
Source−Drain Diode Voltage	V_{SD}	V_{GS} = 0 V, I_S = −200 mA		−0.5		−1.4	V
CHARGES, CAPACITANCES AND GATE RESISTANCE							
Input Capacitance	C_{ISS}	f = 1 MHz, V_{GS} = 0 V V_{DS} = −15 V			13		pF
Output Capacitance	C_{OSS}				3.4		
Reverse Transfer Capacitance	C_{RSS}				1.6		
SWITCHING CHARACTERISTICS, V_{GS} = 4.5 V (Note 4)							
Turn−On Delay Time	$t_{d(ON)}$	V_{GS} = −4.5 V, V_{DD} = −15 V, I_D = −200 mA, R_G = 2.0 Ω			30		ns
Rise Time	t_r				56		
Turn−Off Delay Time	$t_{d(OFF)}$				196		
Fall Time	t_f				145		

4. Switching characteristics are independent of operating junction temperatures

TYPICAL CHARACTERISTICS
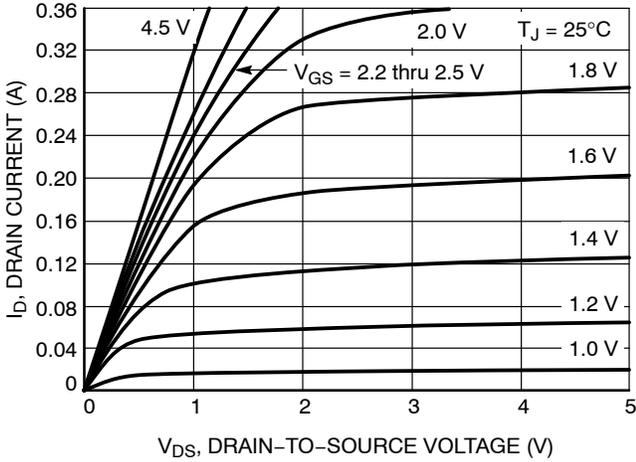
Figure 1. On−Region Characteristics
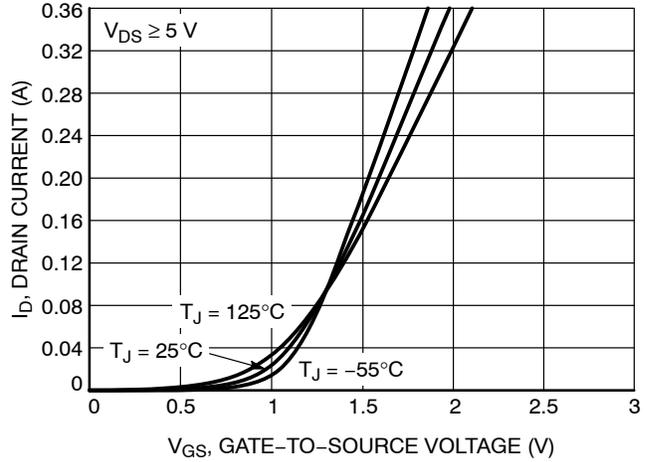
Figure 2. Transfer Characteristics
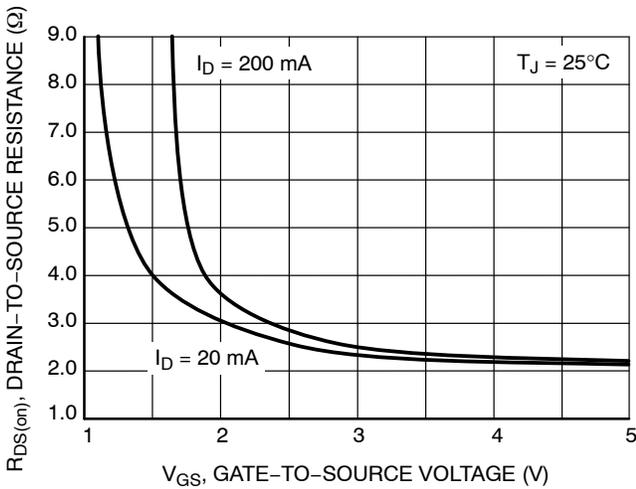
Figure 3. On−Resistance vs. Gate Voltage
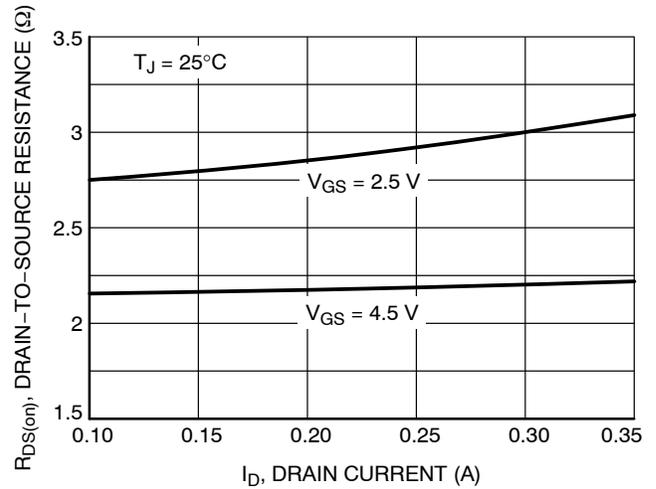
Figure 4. On−Resistance vs. Drain Current and Gate Voltage
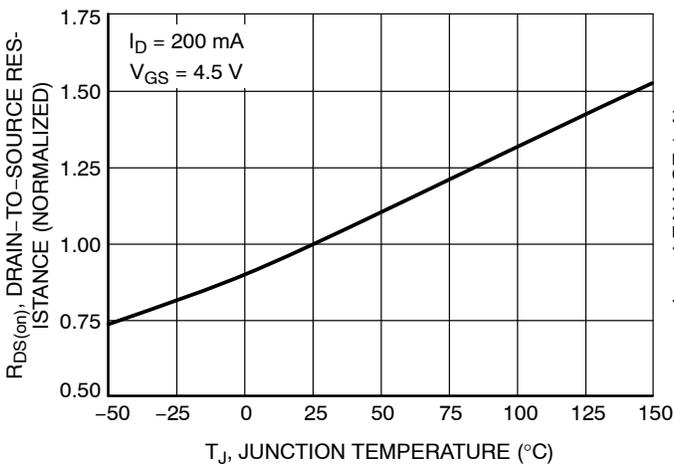
Figure 5. On−Resistance Variation with Temperature
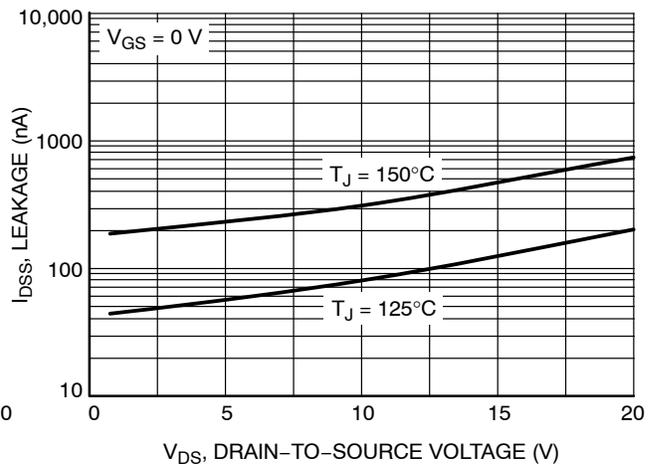
Figure 6. Drain−to−Source Leakage Current vs. Voltage

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TYPICAL CHARACTERISTICS
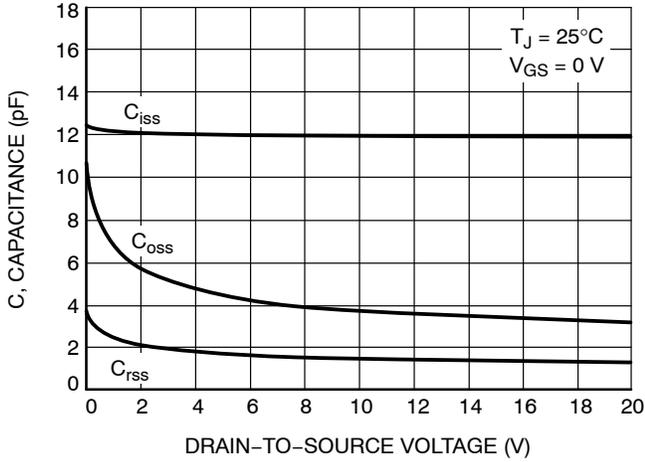
Figure 7. Capacitance Variation
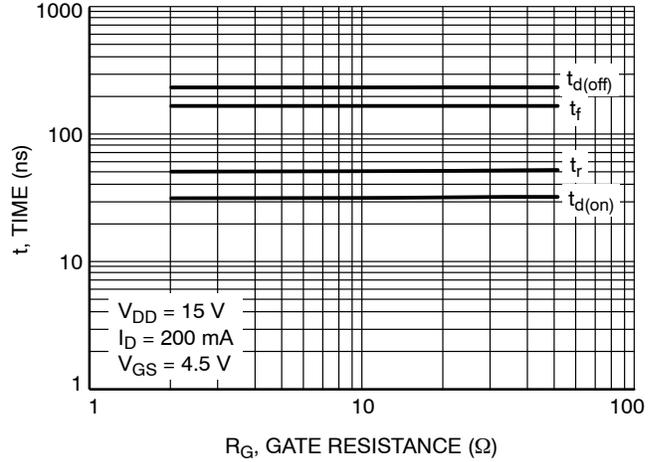
**Figure 8. Resistive Switching Time Variation
vs. Gate Resistance**
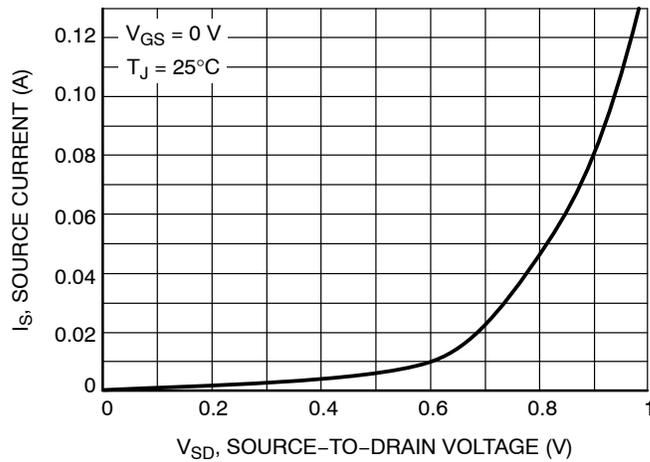
Figure 9. Diode Forward Voltage vs. Current

PACKAGE DIMENSIONS

SOT−1123
CASE 524AA−01
ISSUE B
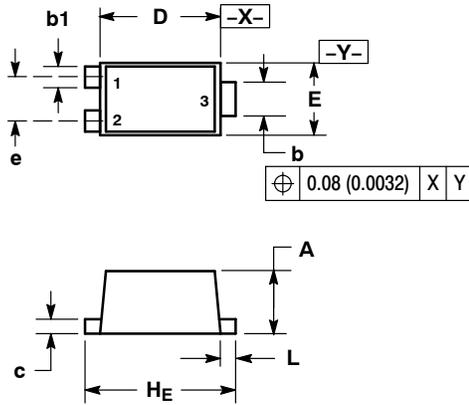
NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.34	0.37	0.40	0.013	0.015	0.016
b	0.15	0.22	0.28	0.006	0.009	0.011
b1	0.10	0.15	0.20	0.004	0.006	0.008
c	0.07	0.12	0.17	0.003	0.005	0.007
D	0.75	0.80	0.85	0.030	0.031	0.033
E	0.55	0.60	0.65	0.022	0.024	0.026
e	0.35	---	0.40	0.014	----	0.016
H_E	0.95	1.00	1.05	0.037	0.039	0.041
L	0.05	0.10	0.15	0.002	0.004	0.006

SOLDERING FOOTPRINT*
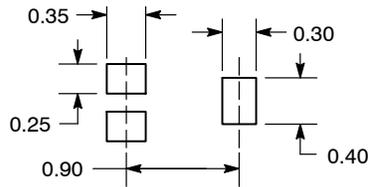
DIMENSIONS: MILLIMETERS

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.